### Maximum Ratings † (TJ = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit	
Peak Repetitive Off-State Voltage (Note 1) $(T_J = -40 \text{ to } 110^{\circ}\text{C}, \text{ Sine Wave, } 50 \text{ to } 60 \text{ Hz, Gate Open})$	2N6394 2N6395 2N6397 2N6399	V <sub>DRM</sub> ,	50 100 400 800	V
On-State RMS Current (180° Conduction Angles; $T_c = 90$ °C)				
Peak Non–Repetitive Surge Current (1/2 Cycle, Sine Wave, 60 Hz, T <sub>J</sub> = 90°C)	I <sub>TSM</sub>	100	А	
Circuit Fusing Considerations (t = 8.3 ms)	l <sub>2t</sub>	40	A²s	
Forward Peak Gate Power (Pulse Width $\leq$ 1.0 $\mu$ s, T <sub>C</sub> = 90°C)	$P_{GM}$	20	W	
Forward Average Gate Power (t = $8.3 \text{ ms}$ , $T_c = 90^{\circ}\text{C}$ )	$P_{G(AV)}$	0.5	W	
Forward Peak Gate Current (Pulse Width $\leq 1.0 \mu s$ , T <sub>C</sub> = 90°C)	I <sub>GM</sub>	2.0	А	
Operating Junction Temperature Range	T <sub>J</sub>	-40 to +125	°C	
Storage Temperature Range		T <sub>stg</sub>	-40 to +125	°C

<sup>†</sup>Indicates JEDEC Registered Data

#### **Thermal Characteristics**

Rating	Symbol	Value	Unit
† Thermal Resistance, Junction to Case	R <sub>suc</sub>	2.0	°C/W
Maximum Lead Temperature for Soldering Purposes, 1/8" from case for 10 seconds	T,	260	°C

<sup>†</sup> Indicates JEDEC Registered Data.

# **Electrical Characteristics - OFF** (TC = 25°C unless otherwise noted; Electricals apply in both directions)

Characteristic		Symbol	Min	Тур	Max	Unit
*Peak Repetitive Blocking Current	T, = 25°C	l <sub>DRM</sub> ,	-	-	1.0	μΑ
$(V_D = V_{DRM} = V_{RRM}; Gate Open)$	$T_J = 100^{\circ}C$	I	-	-	2.0	mA

# **Electrical Characteristics - ON** ( $TC = 25^{\circ}C$ unless otherwise noted; Electricals apply in both directions)

Characteristic	Symbol	Min	Тур	Max	Unit
†Peak Forward On-State Voltage (Note 2) (I <sub>TM</sub> = 24 A Peak)	$V_{TM}$	-	1.7	2.2	V
†Gate Trigger Voltage (Continuous DC), All Quadrants (Continuous dc) ( $V_D = 12 \text{ Vdc}$ , $R_L = 100 \text{ Ohms}$ )	I <sub>GT</sub>	_	5.0	30	mA
†Gate Trigger Voltage (Continuous dc) ( $V_D = 12 \text{ Vdc}$ , $R_L = 100 \text{ Ohms}$ )	V <sub>GT</sub>	-	0.7	1.5	V
Gate Non–Trigger Voltage ( $V_D = 12 \text{ Vdc}$ , $R_L = 100 \text{ Ohms}$ , $T_J = 125 ^{\circ}\text{C}$ )	$V_{GD}$	0.2	_	_	V
†Holding Current ( $V_D = 12 \text{ Vdc}$ , Initiating Current = 200 mA, Gate Open)	I <sub>H</sub>	-	6.0	50	mA
Turn-On Time ( $I_{TM} = 12 \text{ A}, I_{GT} = 40 \text{ mAdc}, V_D = \text{Rated } V_{DRM}$ )	t <sub>at</sub>	_	1.0	2.0	μs
Turn Off Time ( $V_{\rm m}$ = 12 A, $I_{\rm R}$ = 12 A)		-	-	15	
Turn-Off Time ( $V_D$ = Rated $V_{DRM}$ ) ( $I_{TM} = 12 \text{ A}, I_R = 12 \text{ A}, T_J = 125 ^{\circ}\text{C}$ )	T <sub>q</sub>	-	-	35	μs

†Indicates JEDEC Registered Data

2. Pulse Test: Pulse Width  $\leq$  300 µsec, Duty Cycle  $\leq$  2%



Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

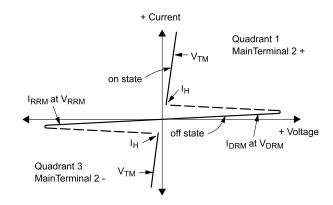
<sup>1.</sup> V<sub>ISBM</sub> and V<sub>ISBM</sub> for all types can be applied on a continuous basis. Ratings apply for zero or negative gate voltage; however, positive gate voltage shall not be applied concurrent with negative potential on the anode. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.

### **Dynamic Characteristics**

Characteristic	Symbol	Min	Тур	Max	Unit
Critical Rate-of-Rise of Off-State Voltage Expovnential $(V_D = Rated V_{DBM}, T_I = 125^{\circ}C)$	dv/dt(c)	-	50	_	V/µs

### Voltage Current Characteristic of Triacs (Bidirectional Device)

Symbol	Parameter
$V_{DRM}$	Peak Repetitive Forward Off State Voltage
I <sub>DRM</sub>	Peak Forward Blocking Current
$V_{RRM}$	Peak Repetitive Reverse Off State Voltage
I <sub>RRM</sub>	Peak Reverse Blocking Current
$V_{TM}$	Maximum On State Voltage
I <sub>L</sub>	Holding Current



**Figure 1. Current Derating** 

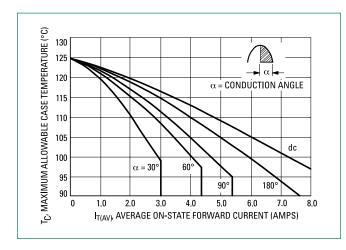


Figure 2. Maximum On-State Characteristics

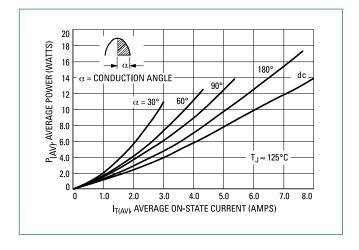


Figure 3. On-State Characteristics

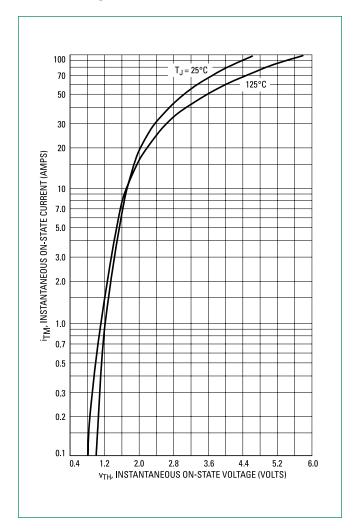


Figure 4. Maximum Non-Repetitive Surge Current

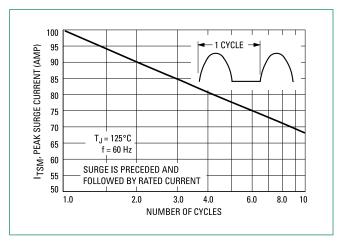
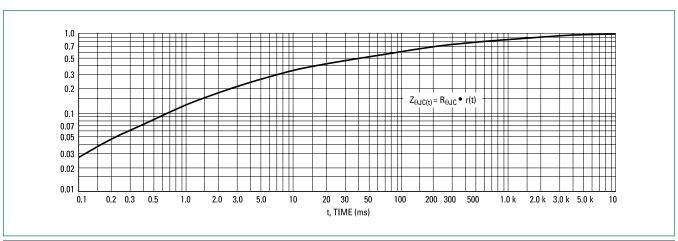


Figure 5. Typical Thermal Response





### **Typical Characteristics**

Figure 6. Typical Gate Trigger Current vs. Pulse Width

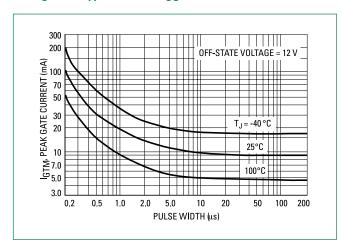


Figure 8. Typical Gate Trigger Voltage vs. Temperature

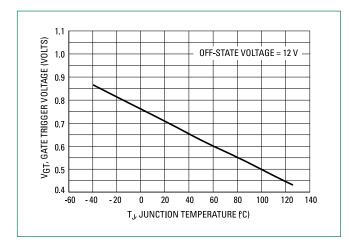


Figure 7. Typical Gate Trigger Current vs. Temperature

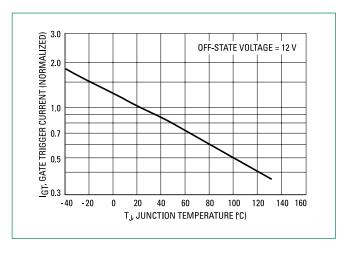
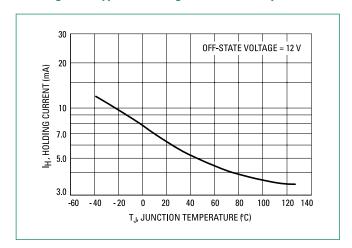


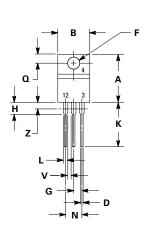
Figure 9. Typical Holding Current vs. Temperature

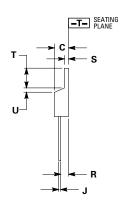


## 2N6394

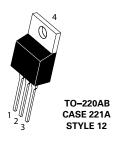
Surface Mount - 50 - 800V

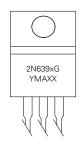
### **Dimensions**





### **Part Marking System**





x =D, M, or N Y =Year

M =Month

A =Assembly Site XX =Lot Serial Code G =Pb-Free Package

D:	Inc	hes	Millimeters		
Dim	Min	Max	Min	Max	
Α	0.590	0.620	14.99	15.75	
В	0.380	0.420	9.65	10.67	
С	0.178	0.188	4.52	4.78	
D	0.025	0.035	0.64	0.89	
F	0.142	0.147	3.61	3.73	
G	0.095	0.105	2.41	2.67	
Н	0.110	0.130	2.79	3.30	
J	0.018	0.024	0.46	0.61	
K	0.540	0.575	13.72	14.61	
L	0.060	0.075	1.52	1.91	
N	0.195	0.205	4.95	5.21	
Q	0.105	0.115	2.67	2.92	
R	0.085	0.095	2.16	2.41	
S	0.045	0.060	1.14	1.52	
T	0.235	0.255	5.97	6.47	
U	0.000	0.050	0.00	1.27	
V	0.045		1.15		
Z		0.080		2.04	

1	Dimanaianian				:1.4 E	1000
١.	Dimensioning	dilu	wierancing	hei	ansi y 14.5m,	1302.

Controlling dimension: inch.

Pin Assignment				
1	Cathode			
2	Anode			
3	Gate			
4	Anode			

### **Ordering Information**

Device	Package	Shipping
2N6394G		1000 Units / Box
2N6394TG		1000 Units / Box
2N6395G	TO-220AB (Pb-Free)	1000 Units / Box
2N6397G		1000 Units / Box
2N6397TG	(1 5 1100)	1000 Units / Box
2N6399G		1000 Units / Box
2N6399TG		1000 Units / Box





<sup>3.</sup> Dimension z defines a zone where all body and lead irregularities are allowed.

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### Littelfuse:

2N6399G 2N6395G 2N6397TG 2N6394G 2N6397G 2N6394TG 2N6399TG